Laboratory:Physics of Electronic Materials 2000-2004

著者	Institute for Materials Research, Tohoku University
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URL	http://hdl.handle.net/10097/56477

Physics of Electronic Materials 2000

Ko, HJ; Chen, YF; Zhu, Z; Yao, T; Kobayashi, I; Uchiki, H

Photoluminescence properties of ZnO epilayers grown on CaF2(111) by plasma assisted molecular beam epitaxy

Appl. Phys. Lett. 76 (2000) 1905 – 1907

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Chen, YF; Hong, SK; Ko, HJ; Nakajima, M; Yao, T; Segawa, Y

Plasma-assisted molecular-beam epitaxy of ZnO epilayers on atomically flat MgAl2O4(111) substrates

Appl. Phys. Lett. 76 (2000) 245 – 247

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Chen, YF; Ko, HJ; Hong, SK; Yao, T

Layer-by-layer growth of ZnO epilayer on Al2O3(0001) by using a MgO buffer layer

Appl. Phys. Lett. 76 (2000) 559 – 561

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Chang, JH; Cho, MW; Wang, HM; Wenisch, H; Hanada, T; Yao, T; Sato, K; Oda, O

Structural and optical properties of high-quality ZnTe homoepitaxial layers

Appl. Phys. Lett. 77 (2000) 1256 – 1258

00-IMR0291

Hong, SK; Hanada, T; Ko, HJ; Chen, Y; Yao, T; Imai, D; Araki, K; Shinohara, M

Control of polarity of ZnO films grown by plasma-assisted molecular-beam epitaxy: Zn- and O-polar ZnO films on Ga-polar GaN templates

Appl. Phys. Lett. 77 (2000) 3571 – 3573

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Ko, HJ; Chen, YF; Hong, SK; Wenisch, H; Yao, T; Look, DC

Ga-doped ZnO films grown on GaN templates by plasma-assisted molecular-beam epitaxy

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Biexciton emission from high-quality ZnO films grown on epitaxial GaN by plasma-assisted molecular-beam epitaxy (vol 77, pg 537, 2000)

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Hong, SK; Yao, T; Kim, BJ; Yoon, SY; Kim, TI

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Nanometer-scale characterization of lateral p-n(+) junction by scanning capacitance microscope

Appl. Surf. Sci. 159 (2000) 210 – 219

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Hong, SK; Ko, HJ; Chen, YF; Hanada, T; Yao, T

Control and characterization of ZnO/GaN heterointerfaces in plasma-assisted MBE-grown ZnO films on GaN/Al2O3

Appl. Surf. Sci. 159 (2000) 441 – 448

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Adsorption processes of Se on the GaAs(111)A-(2x2) surface

Appl. Surf. Sci. 162 (2000) 419 – 424

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Xia, YB; Sekiguchi, T; Zhang, WJ; Jiang, X; Ju, JH; Wang, LJ; Yao, T

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Makino, H; Sasaki, H; Chang, JH; Yao, T

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J. Cryst. Growth 214 (2000) 359 – 363

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J. Cryst. Growth 214 (2000) 581 – 584

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Arai, K; Hanada, T; Yao, T

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J. Cryst. Growth 214 (2000) 703 – 706

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